



IXFL210N30P3 Information



For Reference Only

Part Number IXFL210N30P3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 300V 108A TO-264

Package TO-264-3, TO-264AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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IXFL210N30P3 Specifications

| Manufacturer Part Number IXFL210N30P3 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-264-3, TO-264AA Series HiPerFET?, Polar3? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 300V Current - Continuous Drain (Id) @ 25°C 108A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 268nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 16200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 520W (Tc) |
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| Dds On (May) @ Id Vos |
| Rds On (Max) @ Id, Vgs 16 mOhm @ 105A, 10V |
| Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$ |
| Mounting Type Through Hole |
| Supplier Device Package ISOPLUS264? |
| Package / Case TO-264-3, TO-264AA |
| Report errors? |

IXFL210N30P3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFL210N30P3 Payment Methods



















IXFL210N30P3 Shipping Methods













If you have any question about IXFL210N30P3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com